

ABSTRACT

The invention prevents emitting of a bit of light from an organic EL element and affecting of a display. A gate insulating layer is formed extending on an active layer made of a polysilicon layer which is formed on a transparent insulating substrate made of a glass substrate.

5 A gate extends over the gate insulating layer. An active layer is formed with a source/drain having an LDD structure. A source is formed of a P⁺ layer and a P⁻ layer which are in contact with each other. The P⁺ layer is a high concentration layer of boron as an impurity with concentration of about 1×10^{20} /cc. The P⁻ layer is a low concentration layer containing boron as an impurity with concentration of about 1×10^{18} /cc, and formed extending in a direction between
10 the P⁺ layer and the gate. A drain is also formed of a P⁺ layer and a P⁻ layer which are in contact with each other.